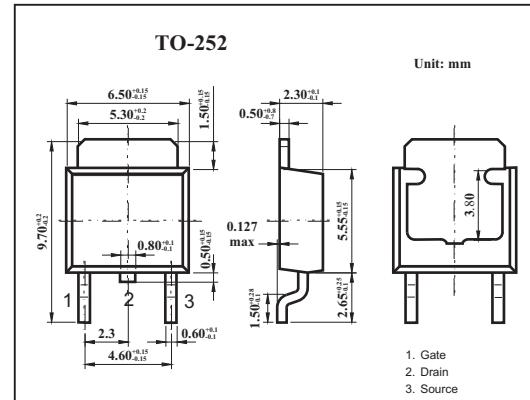
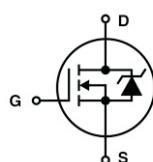


N-Channel MOSFET

KXU05N25

■ Features

- V_{DS} (V) = 250V
- $R_{DS(ON)} \leqslant 1\Omega$ ($V_{GS} = 10V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	250	V
Gate source voltage	V_{GS}	± 20	V
Drain Current — Continuous	I_D	5	A
Drain Current - Pulsed (Note 2)	I_{DM}	15	A
Power dissipation @ $T_a = 25^\circ C$ (Note 1) - Derate above $25^\circ C$	P_D	50 0.32	W $W/^\circ C$
Thermal resistance, junction - ambient	R_{thJA}	100	$^\circ C/W$
Operating and storage temperature	T_j, T_{stg}	-55 to +150	$^\circ C$

Note:1.Power rating when mounted on FR-4 glass epoxy printed circuit board using recommended footprint.

2.Pulse Test : Pulse width $\leqslant 300\mu s$, Duty cycle $\leqslant 2\%$

N-Channel MOSFET

KXU05N25

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BVDSS	VGS = 0 V, ID = 250 μ A	250			V
Gate Threshold Voltage	VGS(th)	VDS = VGS, ID = 250 μ A	2.0		4.0	V
Gate-Body leakage current	IGSS	VGS = ±20 V, VDS = 0 V			±100	nA
Zero Gate Voltage Drain Current	IDSS	VDS = 250 V, VGS = 0 V			10	μ A
Drain-Source On-State Resistance	RDS(on)	VGS = 10 V, ID = 2.5 A		0.81	1	Ω
Forward Transconductance	gFS	VDS = 15 V, ID = 2.5A	1.5	2.6		S
Total Gate Charge	Qg	VDS = 200V ,VGS = 10 V , Id=5 A		13.2	15	nC
Gate-Source Charge	Qgs			2.9		
Gate-Drain Charge	Qgd			6.2		
Input Capacitance	Ciss	VDS =25V ,VGS = 0 , f = 1.0MHz		369	520	pF
Output Capacitance	Coss			66	90	
Reverse Transfer Capacitance	Crss			14	30	
Turn-On Delay Time	td(on)	VDD = 125V ,VGS=10V,RG = 9.1 Ω , ID = 5A		9	10	ns
Turn-On Rise Time	tr			18	40	
Turn-Off Delay Time	td(off)			21	40	
Turn-Off Fall Time	tf			18	40	
Drain-Source Diode Forward Voltage	VSD	Is = 5 A,dIS / dt = 100 A/μs		0.93	1.6	V
Reverse Recovery Time	trr			147		ns
Maximum Body-Diode Continuous Current	Is				5	A

■ Marking

Marking	5N25
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